

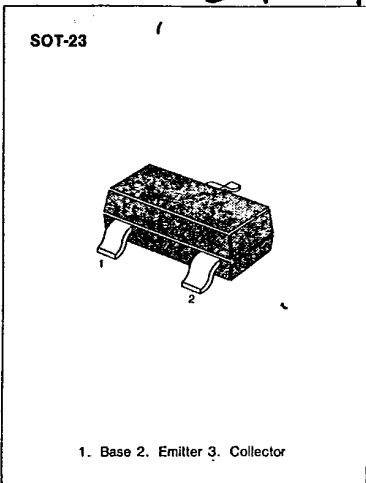
MMBT2907 PNP EPITAXIAL SILICON TRANSISTOR

T-29-19

GENERAL PURPOSE TRANSISTOR

ABSOLUTE MAXIMUM RATINGS (T_a = 25°C)

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V _{CBO}	60	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	5	V
Collector Current	I _C	600	mA
Collector Dissipation	P _C	350	mW
Storage Temperature	T _{stg}	150	°C

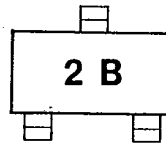


ELECTRICAL CHARACTERISTICS (T_a = 25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector-Base Breakdown Voltage	BV _{CBO}	I _C = 10μA, I _E = 0	60		V
* Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C = 10mA, I _B = 0	40		V
Emitter-Base Breakdown Voltage	BV _{EBO}	I _E = 10μA, I _C = 0	5		V
Collector Cutoff Current	I _{CEX}	V _{CE} = 30V, V _{BE} = 0.5V		50	nA
Collector Cutoff Current	I _{CBO}	V _{CB} = 50V, I _E = 0		0.02	μA
DC Current Gain	h _{FE}	V _{CE} = 10V, I _C = 0.1mA	35		
		V _{CE} = 10V, I _C = 1.0mA	50		
		V _{CE} = 10V, I _C = 10mA	75		
		* V _{CE} = 10V, I _C = 150mA	100	300	
		* V _{CE} = 10V, I _C = 500mA	30		
* Collector-Emitter Saturation Voltage	V _{CE(sat)}	I _C = 150mA, I _B = 15mA		0.4	V
		I _C = 500mA, I _B = 50mA		1.6	V
* Base-Emitter Saturation Voltage	V _{BE(sat)}	I _C = 150mA, I _B = 15mA		1.3	V
		I _C = 500mA, I _B = 50mA		2.6	V
Current Gain-Bandwidth Product	f _T	I _C = 50mA, V _{CE} = 20V f = 100MHz	200		MHz
Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0 f = 1.0MHz		8.0	pF
Turn On Time	t _{on}	V _{CC} = 30V, I _C = 150mA I _{B1} = 15mA		45	ns
Turn Off Time	t _{off}	V _{CC} = 6V, I _C = 150mA I _{B1} = I _{B2} = 15mA		100	ns

*Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

Marking

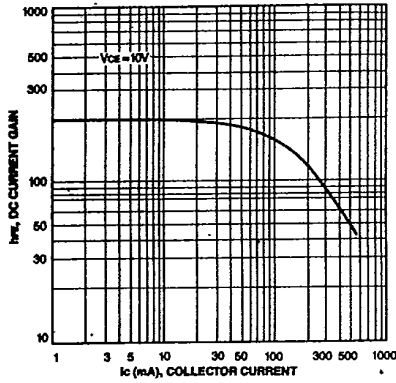


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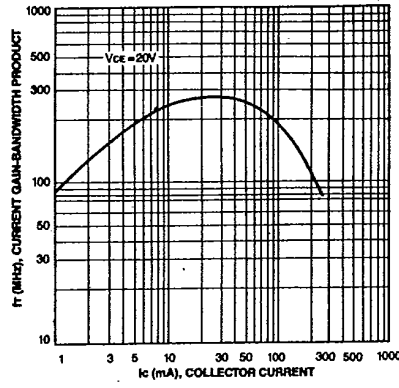
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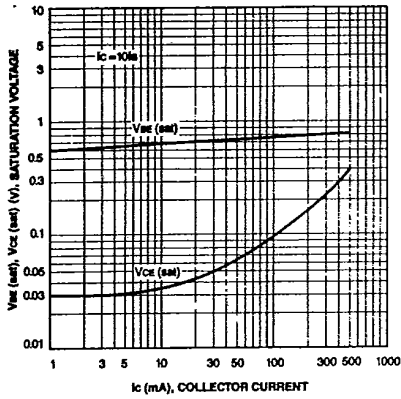
DC CURRENT GAIN



CURRENT GAIN-BANDWIDTH PRODUCT



COLLECTOR-EMITTER SATURATION VOLTAGE
BASE-EMITTER SATURATION VOLTAGE



OUTPUT CAPACITANCE

